RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 1(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W

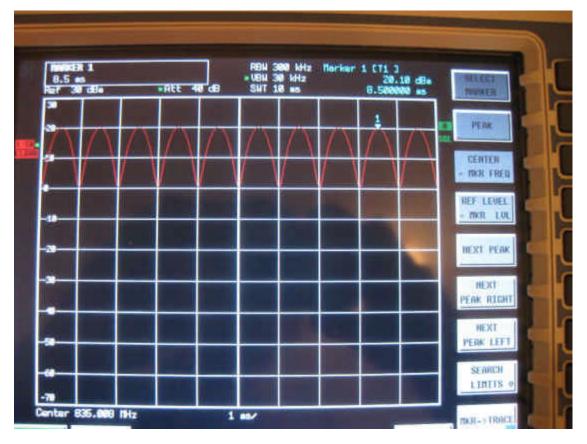
Annex A: Measurement data and plots

A.1 Spectrum analyser plots: CW, 80%AM and GSM signals

	NEEP TIME 18 ms 17 JB cBm	- 466 -		- UBU 3	80 kHz 18 kHz 18 mp	Nerker	1 [11]	10 dBa
3			1				4.520	
.								
-14								
-20	-							
-30								
-•								
-50								
-68-								
-70	ar 835.88							

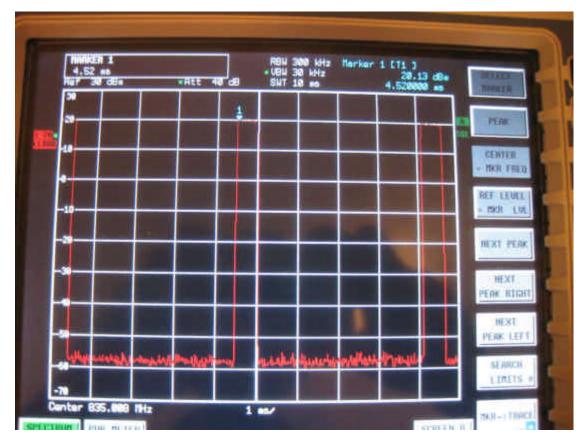
0 Hz Span CW Plot (835MHz)

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 2(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	



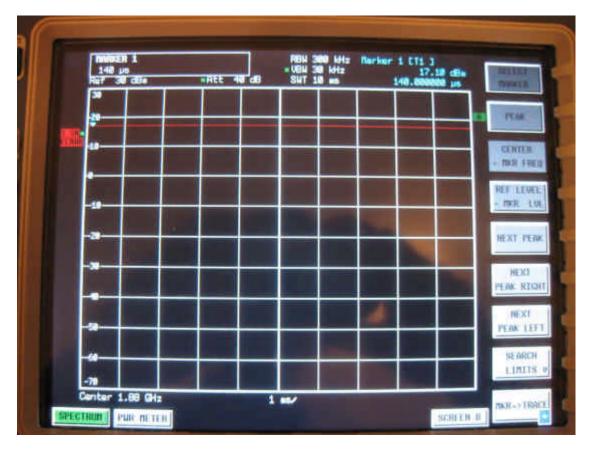
0 Hz Span 80% AM Plot (835MHz)

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 3(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	



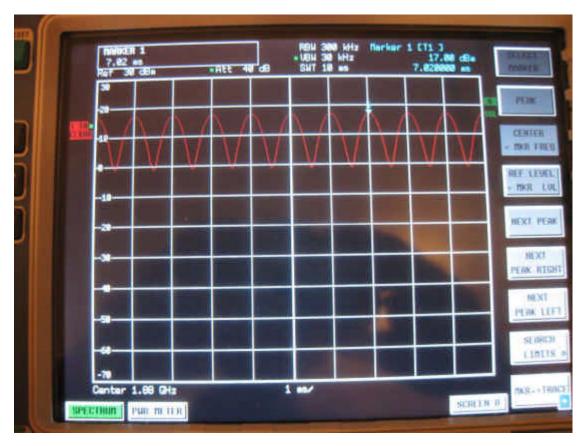
0 Hz Span GSM (835MHz)

RTS RIM Testing Services	Document Annex A to Hearing Aid Report for the BlackBe	l Compatibility RF Emission rry® Smartphone model RE	ns Test 3Z41GW	Page 4(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	



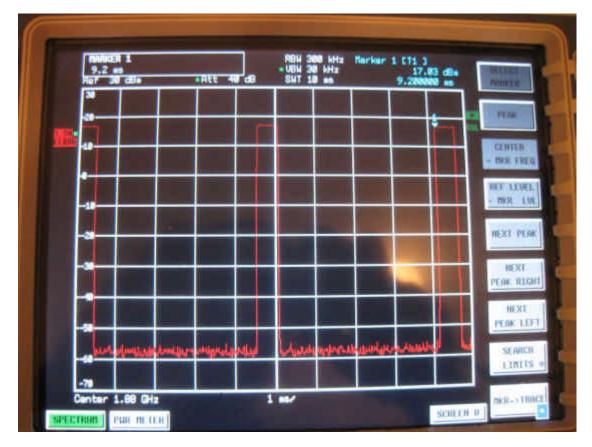
0 Hz Span CW Plot (1880MHz)

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 5(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W



0 Hz Span 80% AM Plot (1880MHz)

RTS RIM Testing Services		I Compatibility RF Emission rry® Smartphone model RE		Page 6(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	



0 Hz Span GSM (1880MHz)

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 7(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	

A.2 Dipole validation and probe modulation factor plots

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 8(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W

Date/Time: 29/07/2008 4:14:47 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW835_20.00dBm.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 113.5 V/m; Power Drift = 0.019 dB Maximum value of Total (measured) = 155.3 V/m

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 9(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 155.5 V/m

Probe Modulation Factor = 1.00

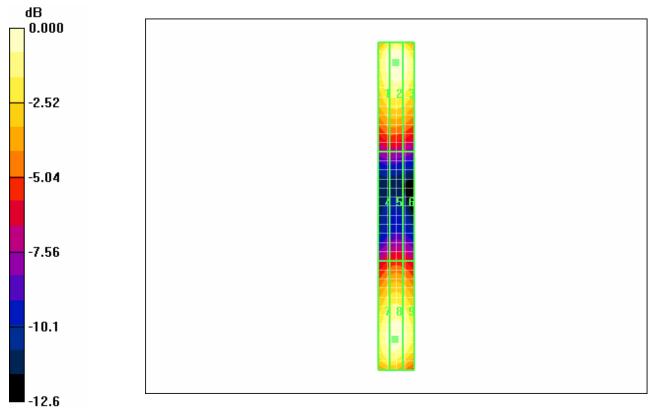
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 113.5 V/m; Power Drift = 0.019 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
150.7	155.5	152.1
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
80.7	82.6	81.1
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
148.0	149.9	146.2
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 10(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	



 $0 \, dB = 155.5 V/m$

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G			W

Date/Time: 26/09/2008 3:00:16 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW835_09_26_08.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 111.5 V/m; Power Drift = -0.138 dB Maximum value of Total (measured) = 148.9 V/m

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 149.5 V/m

Probe Modulation Factor = 1.00

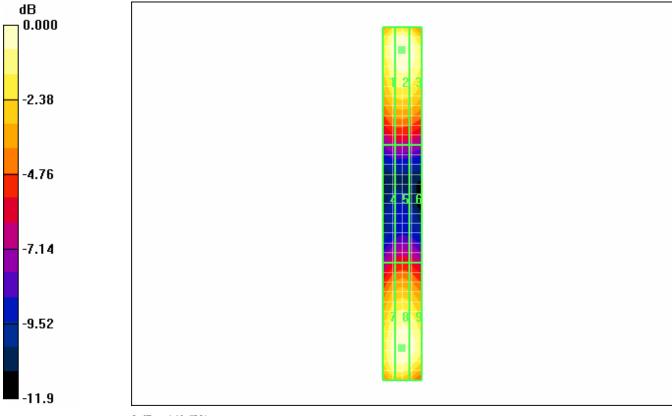
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 111.5 V/m; Power Drift = -0.138 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
146.0	149.5	146.7
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
77.3	79.2	77.5
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
144.6	148.2	145.0
Μ	\mathbf{M}	Μ
4	4	4

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 13(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



 $0 \ dB = 149.5 V/m$

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV			W

Date/Time: 26/09/2008 2:26:11 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW835_PMF_GSM.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 115.1 V/m; Power Drift = -0.023 dB Maximum value of Total (measured) = 157.1 V/m

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 157.7 V/m

Probe Modulation Factor = 1.00

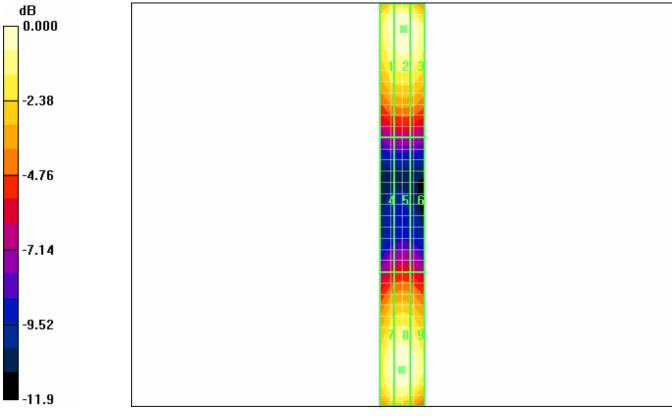
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 115.1 V/m; Power Drift = -0.023 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
154.0	157.7	155.7
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
81.4	83.3	81.8
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
152.3	156.3	152.8
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 16(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G ¹		W	



0 dB = 157.7 V/m

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 17(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 26/09/2008 2:34:29 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_AM835_PMF_GSM.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 71.6 V/m; Power Drift = 0.109 dB Maximum value of Total (measured) = 98.3 V/m

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 18(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G			W

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 98.6 V/m

Probe Modulation Factor = 1.00

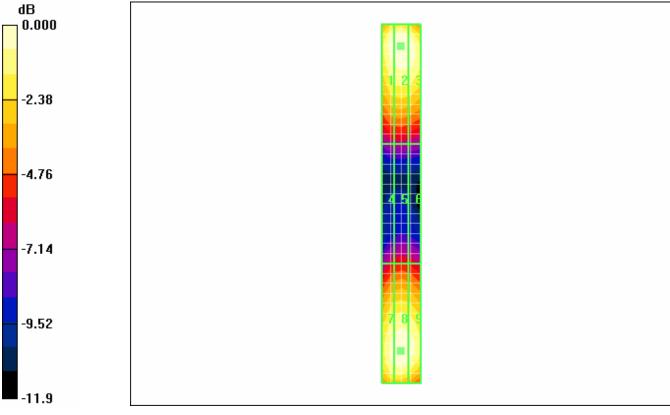
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 71.6 V/m; Power Drift = 0.109 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
97.3	98.6	97.1
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
51.5	52.6	51.6
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
94.9	97.1	95.2
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 19(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



 $0 \, dB = 98.6 \text{V/m}$

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 20(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 27/09/2008 7:54:48 AM

Test Laboratory: RTS File Name: HAC_E_Dipole_GSM835.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: GSM 850; Frequency: 835 MHz;Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 35.3 V/m; Power Drift = 0.054 dB Maximum value of Total (measured) = 53.4 V/m

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 21(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 53.6 V/m

Probe Modulation Factor = 1.00

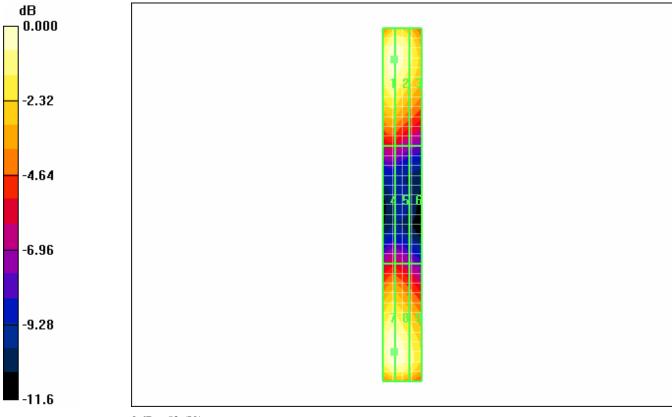
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 35.3 V/m; Power Drift = 0.054 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
52.3	52.2	46.7
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
27.8	27.7	24.1
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
53.6	53.4	47.8
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 22(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



0 dB = 53.6 V/m

RTS RIM Testing Services			Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W	

Date/Time: 29/07/2008 3:59:04 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW1880_20.00dBm.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 116.8 V/m; Power Drift = -0.007 dB Maximum value of Total (measured) = 123.4 V/m

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 24(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 124.9 V/m

Probe Modulation Factor = 1.00

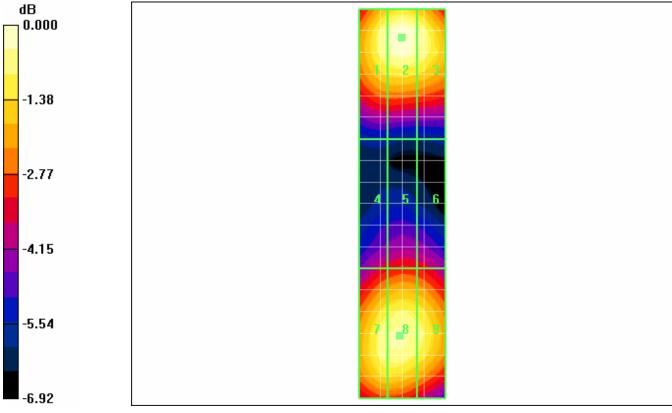
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 116.8 V/m; Power Drift = -0.007 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
120.7	124.9	121.0
Μ	Μ	Μ
2	2	2
Grid 4	Grid 5	Grid 6
85.1	88.0	86.6
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
118.1	119.6	115.8
Μ	Μ	Μ
2	2	2

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G ¹		W	



0 dB = 124.9 V/m

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 26/09/2008 12:51:51 PM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW1880_20.00dBm_26_09_08.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 123.4 V/m; Power Drift = 0.006 dB Maximum value of Total (measured) = 123.6 V/m

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 125.9 V/m

Probe Modulation Factor = 1.00

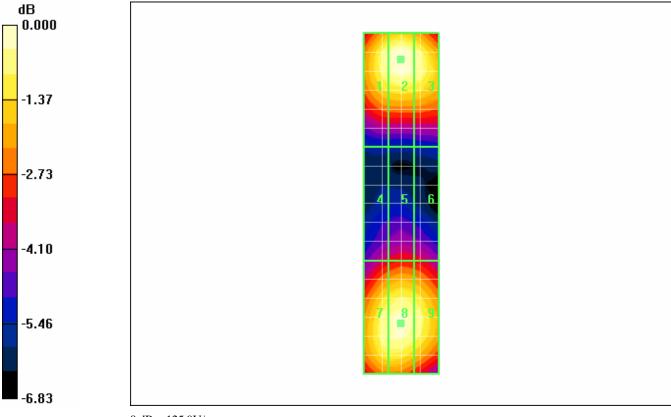
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 123.4 V/m; Power Drift = 0.006 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
122.2	125.9	122.0
Μ	Μ	Μ
2	2	2
Grid 4	Grid 5	Grid 6
84.7	88.0	86.7
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
120.5	122.4	119.0
Μ	Μ	Μ
2	2	2

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 28(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



 $0 \ dB = 125.9 V/m$

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 29(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 27/09/2008 8:32:36 AM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW1880_PMF.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 85.6 V/m; Power Drift = -0.006 dB Maximum value of Total (measured) = 84.2 V/m

E Scan - measurement distance from the probe sensor center to

RTS RIM Testing Services	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 30(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 85.8 V/m

Probe Modulation Factor = 1.00

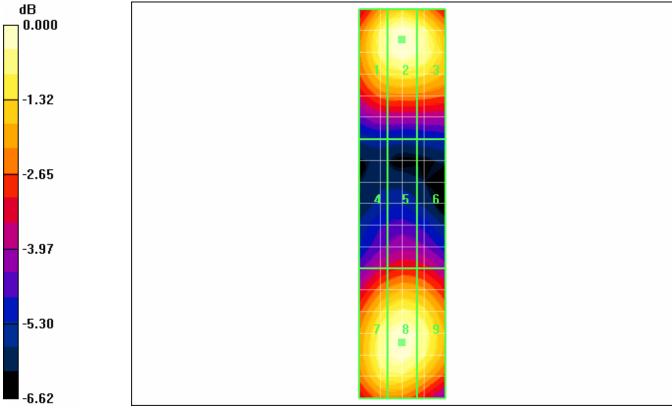
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 85.6 V/m; Power Drift = -0.006 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
83.2	85.8	83.8
Μ	Μ	Μ
3	3	3
Grid 4	Grid 5	Grid 6
58.6	60.7	60.0
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
82.8	84.5	82.3
Μ	Μ	Μ
3	3	3

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 31(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



 $0 \ dB = 85.8 V/m$

RTS RIM Testing Services	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 32(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G ¹		W	

Date/Time: 26/09/2008 1:12:00 PM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_AM_1880_PMF_GSM.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 56.2 V/m; Power Drift = 0.021 dB Maximum value of Total (measured) = 56.5 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 33(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 57.5 V/m

Probe Modulation Factor = 1.00

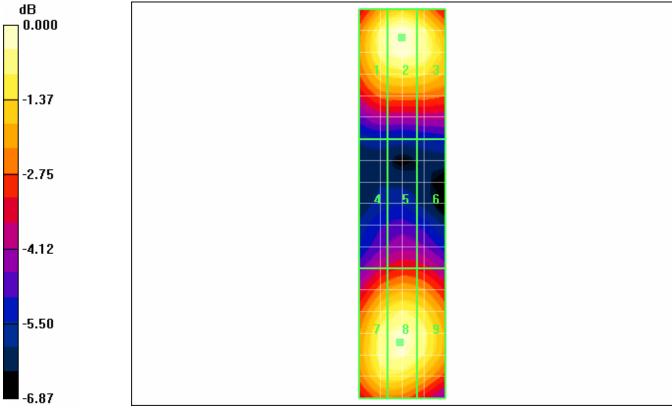
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 56.2 V/m; Power Drift = 0.021 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
55.9	57.5	55.8
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
38.8	40.2	39.6
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
54.9	55.8	54.2
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 34(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



0 dB = 57.5 V/m

RTS RIM Testing Services	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 35(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 27/09/2008 8:16:05 AM

Test Laboratory: RTS File Name: HAC_E_Dipole_GSM1880.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 29.2 V/m; Power Drift = -0.047 dB Maximum value of Total (measured) = 28.9 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 36(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 29.5 V/m

Probe Modulation Factor = 1.00

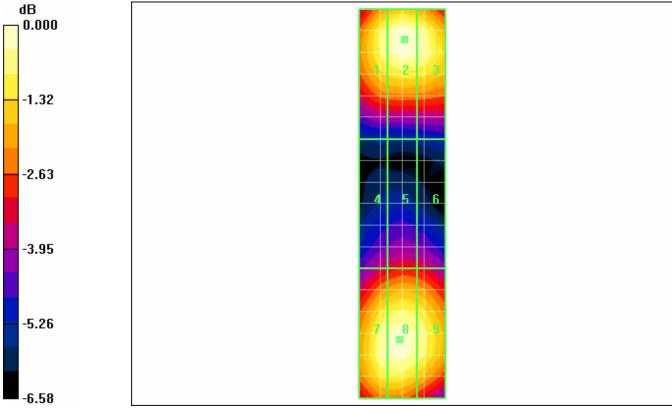
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 29.2 V/m; Power Drift = -0.047 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
28.3	29.5	28.9
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
20.1	20.9	20.6
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
28.6	29.0	28.0
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 37(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



 $0 \ dB = 29.5 V/m$

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 38(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 29/07/2008 4:27:42 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW835_20.00dBm.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.460 A/m; Power Drift = 0.001 dB Maximum value of Total (measured) = 0.437 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 39(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.438 A/m

Probe Modulation Factor = 1.00

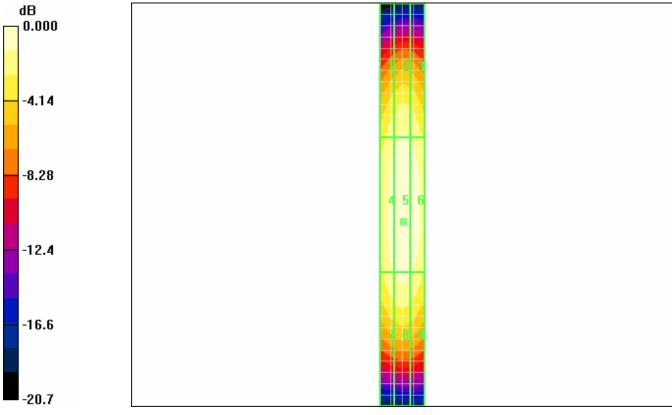
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.460 A/m; Power Drift = 0.001 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.362	0.384	0.374
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
0.411	0.438	0.426
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
0.377	0.395	0.381
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 40(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



0 dB = 0.438 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 41(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 26/09/2008 4:28:20 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW835_20dBm_09_26_08.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.446 A/m; Power Drift = 0.070 dB Maximum value of Total (measured) = 0.425 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 42(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.427 A/m

Probe Modulation Factor = 1.00

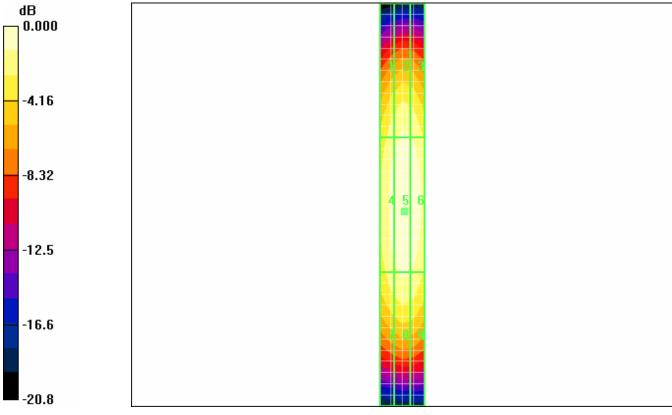
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.446 A/m; Power Drift = 0.070 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1 0.351	Grid 2 0.376	Grid 3 0.369
M 4	M 4	M 4
Grid 4	Grid 5	Grid 6
0.393	0.427	0.418
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
0.351	0.377	0.367
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 43(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



 $0 \, dB = 0.427 \, A/m$

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 44(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 26/09/2008 3:58:11 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW835_PMF_GSM.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.472 A/m; Power Drift = 0.082 dB Maximum value of Total (measured) = 0.445 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		Page 45(126)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.447 A/m

Probe Modulation Factor = 1.00

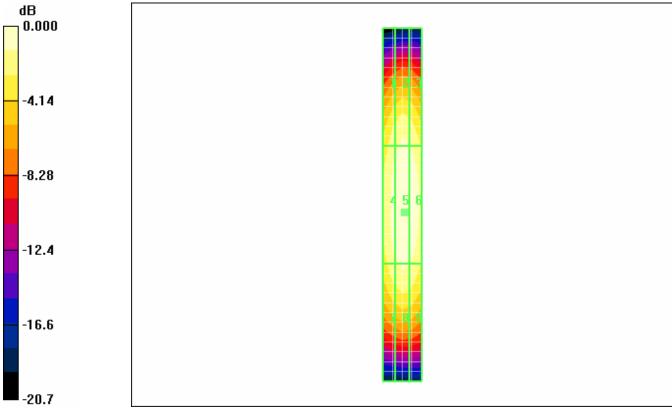
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.472 A/m; Power Drift = 0.082 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.370	0.396	0.386
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
0.413	0.447	0.438
M	M	M
4	4	4
Grid 7	Grid 8	Grid 9
0.373	0.395	0.384
M	M	M
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 46(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



0 dB = 0.447 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 47(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 26/09/2008 4:06:30 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_AM835_PMF_GSM.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.299 A/m; Power Drift = -0.023 dB Maximum value of Total (measured) = 0.282 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 48(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.283 A/m

Probe Modulation Factor = 1.00

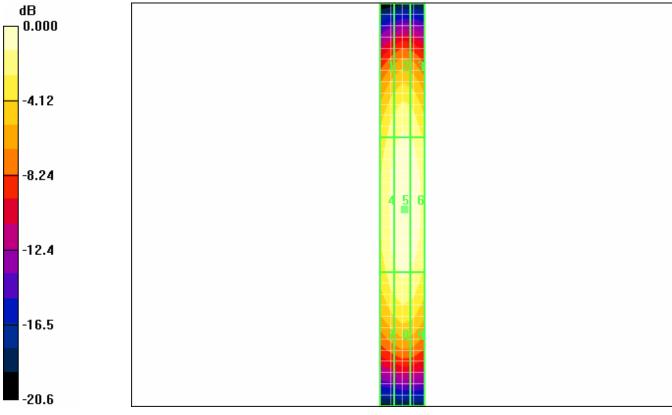
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.299 A/m; Power Drift = -0.023 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1 0.232	Grid 2 0.249	Grid 3 0.243
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
0.259	0.283	0.277
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
0.234	0.250	0.242
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 49(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



0 dB = 0.283 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 50(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 27/09/2008 7:31:31 AM

Test Laboratory: RTS File Name: HAC_H_Dipole_GSM835.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 850; Frequency: 835 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.171 A/m; Power Drift = 0.107 dB Maximum value of Total (measured) = 0.163 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 51(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.164 A/m

Probe Modulation Factor = 1.00

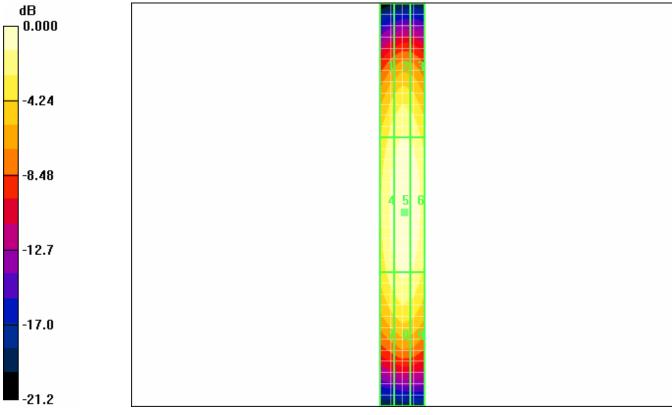
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.171 A/m; Power Drift = 0.107 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.132	0.142	0.138
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
0.150	0.164	0.160
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
0.135	0.145	0.140
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 52(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



0 dB = 0.164 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 53(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 29/07/2008 4:35:58 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW1880_20.00dBm.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.467 A/m; Power Drift = 0.014 dB Maximum value of Total (measured) = 0.444 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 54(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.445 A/m

Probe Modulation Factor = 1.00

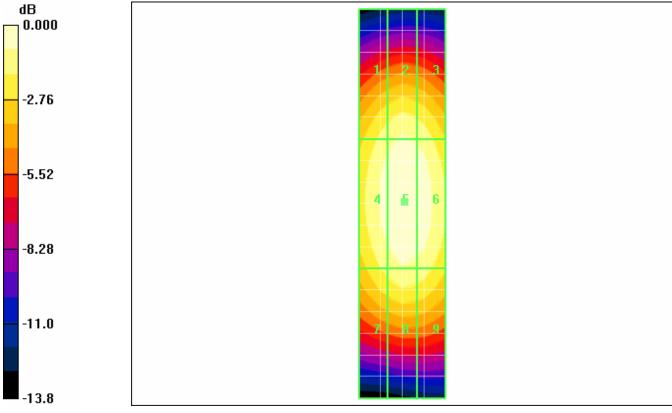
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.467 A/m; Power Drift = 0.014 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.385	0.407	0.396
Μ	Μ	Μ
2	2	2
Grid 4	Grid 5	Grid 6
0.419	0.445	0.434
Μ	Μ	\mathbf{M}
2	2	2
Grid 7	Grid 8	Grid 9
0.374	0.396	0.387
Μ	Μ	Μ
2	2	2

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 55(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



0 dB = 0.445 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 56(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 26/09/2008 5:27:46 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_CW1880_20dBm_09_26_08.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.463 A/m; Power Drift = 0.004 dB Maximum value of Total (measured) = 0.439 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 57(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.442 A/m

Probe Modulation Factor = 1.00

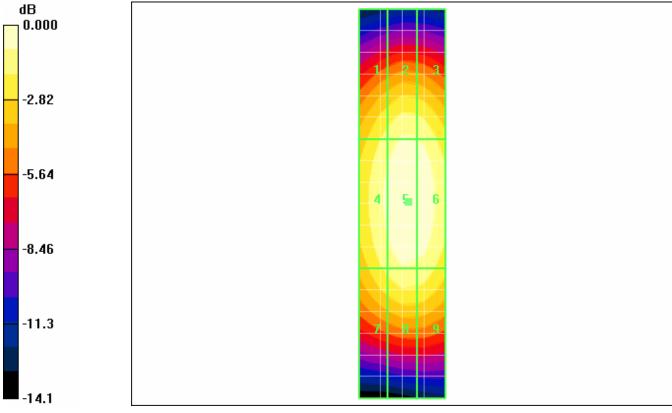
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.463 A/m; Power Drift = 0.004 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.373	0.404	0.399
Μ	Μ	Μ
2	2	2
Grid 4	Grid 5	Grid 6
0.408	0.442	0.436
Μ	Μ	\mathbf{M}
2	2	2
Grid 7	Grid 8	Grid 9
0.367	0.394	0.388
Μ	Μ	Μ
2	2	2

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 58(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



0 dB = 0.442 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 59(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 26/09/2008 5:05:10 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW1880_PMF_GSM.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.336 A/m; Power Drift = -0.004 dB Maximum value of Total (measured) = 0.319 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 60(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.321 A/m

Probe Modulation Factor = 1.00

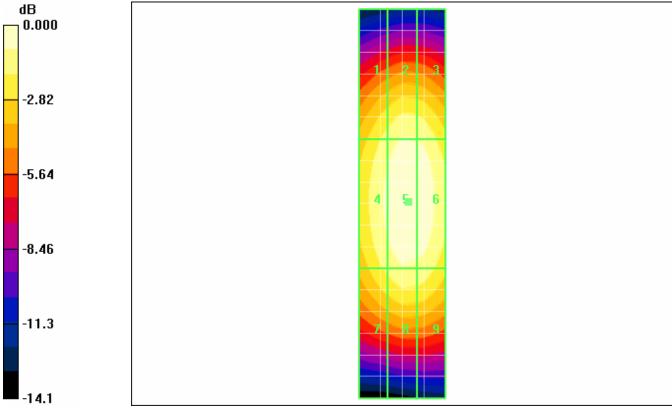
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.336 A/m; Power Drift = -0.004 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.270	0.292	0.289
Μ	Μ	Μ
3	3	3
Grid 4	Grid 5	Grid 6
0.296	0.321	0.316
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
0.266	0.286	0.282
Μ	Μ	Μ
3	3	3

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 61(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



0 dB = 0.321 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 62(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 26/09/2008 5:09:43 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_AM1880_PMF_GSM.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.216 A/m; Power Drift = 0.018 dB Maximum value of Total (measured) = 0.204 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 63(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.205 A/m

Probe Modulation Factor = 1.00

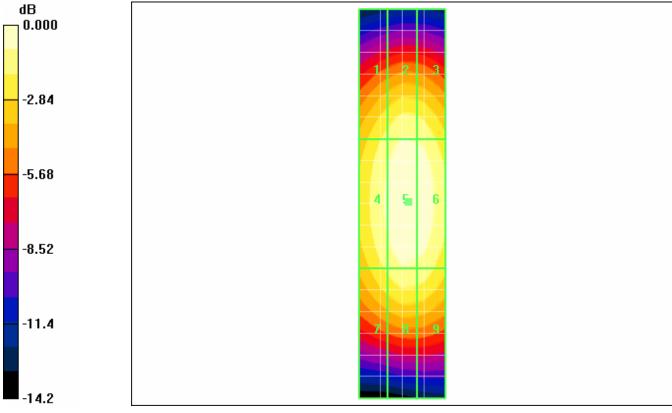
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.216 A/m; Power Drift = 0.018 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.172	0.186	0.184
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
0.188	0.205	0.202
Μ	Μ	Μ
4	3	3
Grid 7	Grid 8	Grid 9
0.169	0.183	0.180
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 64(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1 L6ARBZ40GW		W



0 dB = 0.205 A/m

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 65(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W

Date/Time: 27/09/2008 7:22:26 AM

Test Laboratory: RTS File Name: HAC_H_Dipole_GSM1880.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(5x19x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.125 A/m; Power Drift = -0.027 dB Maximum value of Total (measured) = 0.117 A/m

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 66(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W

CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.117 A/m

Probe Modulation Factor = 1.00

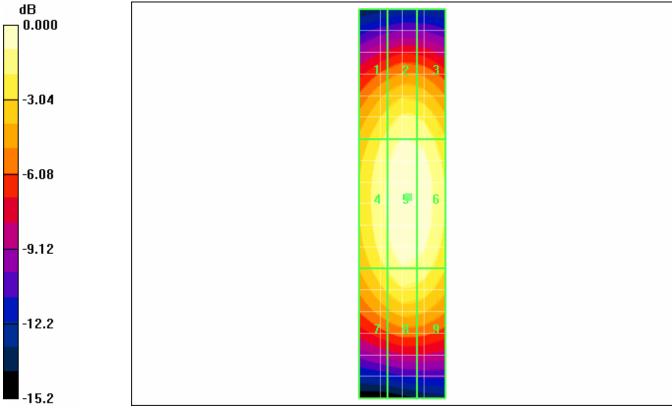
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.125 A/m; Power Drift = -0.027 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in	A/m	
Grid 1 0.096 M	Grid 2 0.106 M	Grid 3 0.104 M
4	4	4
Grid 4	Grid 5	Grid 6
0.107	0.117	0.115
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
0.094	0.104	0.101
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 67(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GW		W	

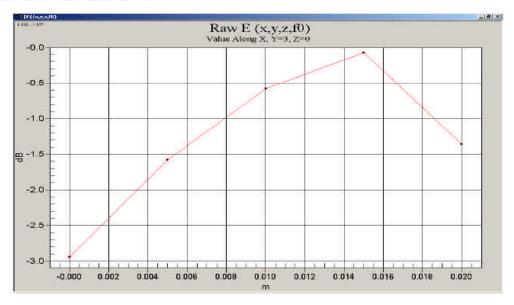


0 dB = 0.117 A/m

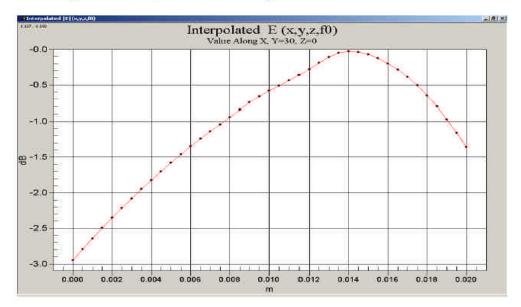
RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 68(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	

Justification of Step Size and Interpolation

This section demonstrates that a 5mm step size with interpolation provides sufficient resolution for RF emissions measurements. The DASY 4 uses interpolation algorithms to derive 9 interpolated points between every measured point.

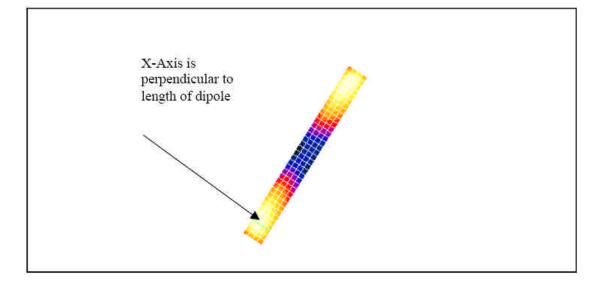


The figure above shows the raw measured field strength perpendicular to the length of the validation dipole. The TCB guidance slides require the 3dB width to be much larger than the step size. The width between -3dB points is > 21mm, at least 4 times the step size.



This figure shows the interpolated field strength perpendicular to the dipole. The interpolated points follow the raw points with no inconsistencies.

RTS RIM Testing Services	Document Annex A to Hearing Aid Report for the BlackBer	l Compatibility RF Emission rry® Smartphone model RE	ns Test 3Z41GW	Page 69(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GW		W	



The green line in this figure shows the axis along which the points lie.

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 70(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W

Date/Time: 14/07/2005 11:35:24 AM

Page 1 of 2

Date/Time: 14/07/2005 11:35:24 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m³ Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

Phatomit HAC Test Arch; Type: SD HAC P01 BA;
 Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm Maximum value of Total field (slot averaged) = 131.0 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

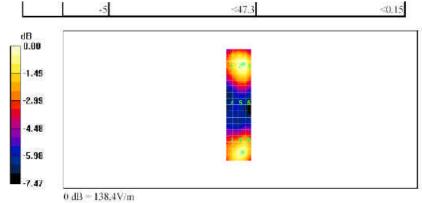
E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1 123.2	Grid 2 138.1			Grid 3 1 38.4
Grid 4 80.9		 	Grid 4 80.9	Grid 6 92.2
Grid 7 119.8				Grid 9 1 30.7

Categor	y AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print Templates\Dipole%20Validation%201880%20... 14/07/2005

RTS RIM Testing Services	ons Test RBZ41GW	Page 71(126)		
Author Data	Dates of Test	Report No DTS 1115 0800 31 Dow 1	FCC ID	w
Daoud Attayi Date/Time: 14	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	Page 2 of 2	W
	na n	(201		



file://C:\Program%20Files\DASY4\Print_Templates\Dipole%20Validation%201880%20... 14/07/2005

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 72(126)
Author Data Daoud Attayi	Dates of Test Report No FCC ID July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 14/07/2005 11:44:51 AM

Page 1 of 2

Date/Time: 14/07/2005 11:44:51 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m³ Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

Phatomit HAC Test Arch; Type: SD HAC P01 BA;
 Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm Maximum value of Total field (slot averaged) = 131.2 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
123.1	138.6	138.6	123.1	138.6	138.6
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
81.4	92.1	91.6	81.4	92.1	91.6
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
121.3	131.2	131.0	121.3	131.2	131.0

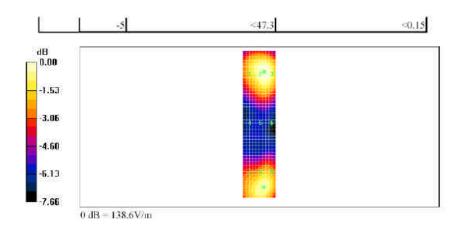
Categor	y AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
М1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print Templates\Dipole%20Validation%201880%20... 14/07/2005

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 73(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G			N

Date/Time: 14/07/2005 11:44:51 AM

Page 2 of 2



file://C?Program%20Files/DASY4Print_Templates/Dipole%20Validation%201880%20... 14/07/2005

RTS	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 74(126)
RIM Testing Services				
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV			W

Date/Time: 14/07/2005 12:43:02 PM

Page 1 of 2

Date/Time: 14/07/2005 12:43:02 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_5 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m³ Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: Omm (Fix Surface) Sensor-Surface: (Fix Surface)
 Electronics: DAE3 Sn472; Calibrated: 03/01/2005

Phantom: HAC Test Arch; Type: SD HAC P01 BA;
 Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):

Measurement grid: dx=5mm, dy=5mm Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

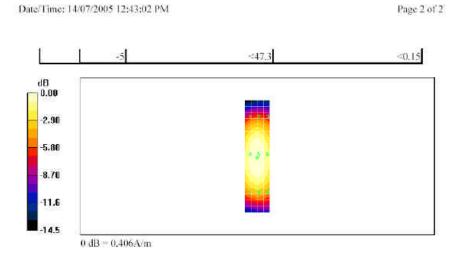
H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3
0.342	0.359	0.344
Grid 4	Grid 5	Grid 6
0.389	0.406	0.389
Grid 7	Grid 8	Grid 9
0.363	0.378	0.363

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print_Templates\HAC_H_Dipole_CW%201880_5%... 14/07/2005

RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	l Compatibility RF Emission rry® Smartphone model RI	ns Test 3Z41GW	Page 75(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	



lile://C:\Program%20Files\DASY4\Print_Templates\HAC_H_Dipole_CW%201880_5%... 14/07/2005

RIM Testing Services Author Data Daoud Attayi	Dates of Test July 29, Sep 26-27, 2008	76(126) W			
RTS	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW				

Date/Time: 14/07/2005 12:53:40 PM

Page 1 of 2

Date/Time: 14/07/2005 12:53:40 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m³ Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

Phatomi: HAC Test Arch; Type: SD HAC P01 BA;
 Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):

Measurement grid: dx=2mm, dy=2mm Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

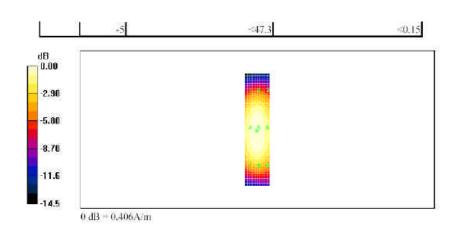
H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
0.347	0.361	0.348	0.347	0.361	0.348
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
0.394	0.406	0.391	0.394	0.406	0.391
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
0.367	0.380	0.365	0.367	0.380	0.365

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print Templates\HAC H Dipole CW%201880 2%... 14/07/2005

77(126)
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file://C:\Program%20Files\DASY4\Print_Templates\HAC_H_Dipole_CW%201880_2%... 14/07/2005

RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	l Compatibility RF Emission rry® Smartphone model RE	ns Test 3Z41GW	Page 78(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV			W

A.3 RF emissions and ambient noise plots

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 79(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV			W

Date/Time: 29/07/2008 6:59:23 PM

Test Laboratory: RTS File Name: HAC_E_GSM850_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 75.9 V/m; Power Drift = -0.082 dB Maximum value of Total (measured) = 61.3 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RB		Page 80(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	-31 Rev 1 L6ARBZ40GW	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 181.1 V/m

Probe Modulation Factor = 2.94

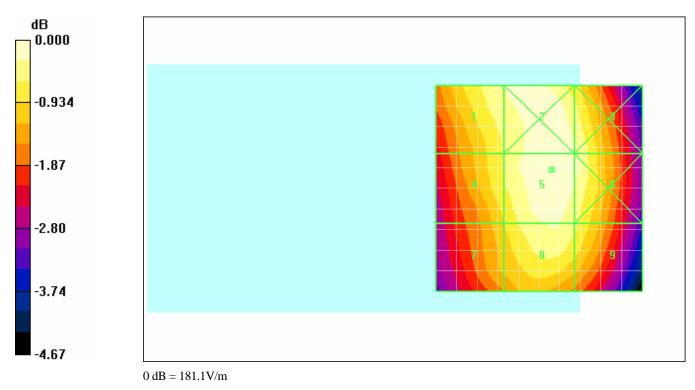
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 75.9 V/m; Power Drift = -0.082 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
174.3	180.0	176.1
Μ	Μ	Μ
3	3	3
Grid 4	Grid 5	Grid 6
169.3	181.1	176.8
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
162.7	175.3	170.3
Μ	Μ	Μ
3	3	3

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 81(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 29/07/2008 7:05:11 PM

Test Laboratory: RTS File Name: HAC_E_GSM850_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 836.8 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 83.3 V/m; Power Drift = 0.121 dB Maximum value of Total (measured) = 69.7 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RB		Page 83(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 205.0 V/m

Probe Modulation Factor = 2.94

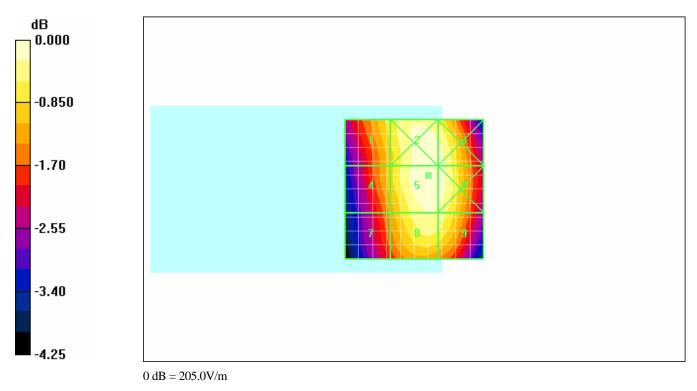
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 83.3 V/m; Power Drift = 0.121 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
189.7	204.4	202.8
Μ	Μ	Μ
3	3	3
Grid 4	Grid 5	Grid 6
184.3	205.0	203.4
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
176.7	198.6	197.2
Μ	Μ	Μ
3	3	3

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 85(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 29/07/2008 7:18:12 PM

Test Laboratory: RTS

File Name: <u>HAC_E_GSM850_High_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 85.0 V/m; Power Drift = 0.034 dB Maximum value of Total (measured) = 71.3 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RB		Page 86(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 209.8 V/m

Probe Modulation Factor = 2.94

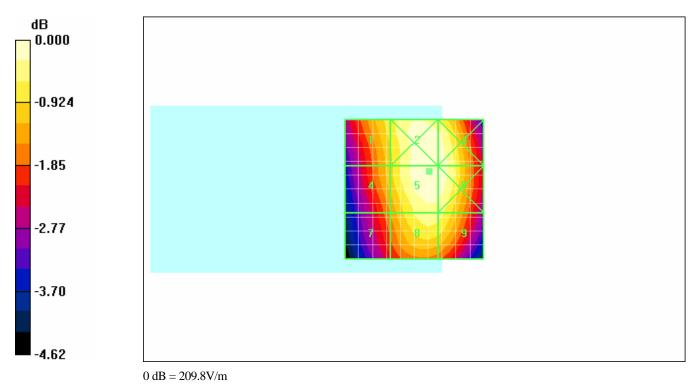
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 85.0 V/m; Power Drift = 0.034 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
193.1	209.4	208.3
Μ	Μ	Μ
3	3	3
Grid 4	Grid 5	Grid 6
187.0	209.8	208.4
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
176.6	200.0	198.7
Μ	Μ	Μ
3	3	3

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 87(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 88(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 29/07/2008 7:29:27 PM

Test Laboratory: RTS File Name: HAC_E_GSM1900_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 13.9 V/m; Power Drift = -0.096 dB Maximum value of Total (measured) = 24.6 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RB		Page 89(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40G	W

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 66.1 V/m

Probe Modulation Factor = 2.91

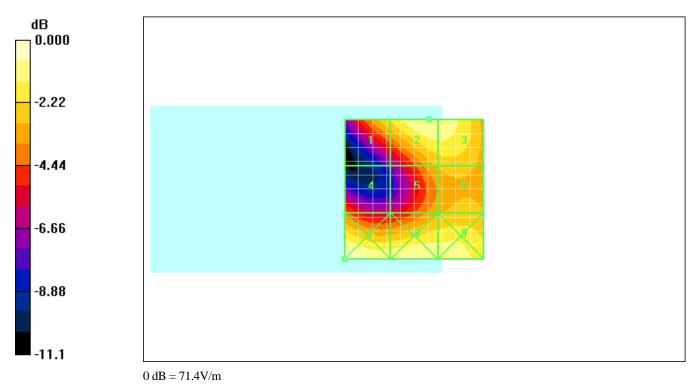
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 13.9 V/m; Power Drift = -0.096 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
57.0	66.1	65.6
Μ	Μ	\mathbf{M}
3	3	3
Grid 4	Grid 5	Grid 6
45.0	51.7	53.2
Μ	Μ	Μ
4	3	3
Grid 7	Grid 8	Grid 9
71.4	66.8	65.1
Μ	Μ	Μ
3	3	3

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 90(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 91(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G ¹			W

Date/Time: 29/07/2008 7:35:13 PM

Test Laboratory: RTS File Name: HAC_E_GSM1900_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 15.4 V/m; Power Drift = 0.020 dB Maximum value of Total (measured) = 28.6 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services	Report for the BlackBe	l Compatibility RF Emission rry® Smartphone model RE		Page 92(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 61.4 V/m

Probe Modulation Factor = 2.91

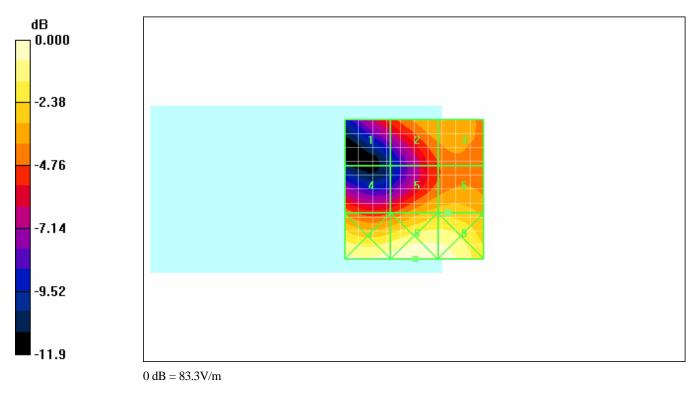
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 15.4 V/m; Power Drift = 0.020 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
46.2	57.8	58.0
Μ	Μ	Μ
4	3	3
Grid 4	Grid 5	Grid 6
51.6	60.8	61.4
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
80.3	83.3	81.2
Μ	Μ	Μ
3	3	3

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 93(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 94(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 29/07/2008 7:41:12 PM

Test Laboratory: RTS

File Name: HAC_E_GSM1900_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1909.8 MHz;Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 16.7 V/m; Power Drift = -0.030 dB Maximum value of Total (measured) = 29.3 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services	Report for the BlackBe	l Compatibility RF Emission rry® Smartphone model RE		Page 95(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 65.3 V/m

Probe Modulation Factor = 2.91

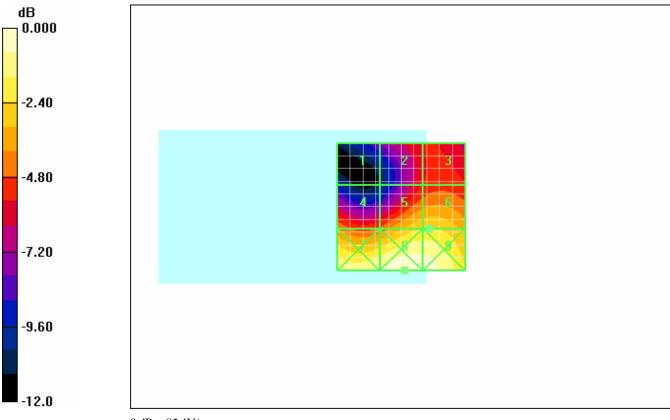
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 16.7 V/m; Power Drift = -0.030 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
34.7	45.5	48. 1
Μ	Μ	Μ
4	4	3
Grid 4	Grid 5	Grid 6
54.2	64.8	65.3
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
80.2	85.4	83.5
Μ	Μ	Μ
3	2	3

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 96(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	





RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 97(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV			W

Date/Time: 29/07/2008 6:31:43 PM

Test Laboratory: RTS

File Name: HAC_H_GSM850_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.072 A/m; Power Drift = 0.136 dB Maximum value of Total (measured) = 0.140 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RB		Page 98(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.365 A/m

Probe Modulation Factor = 2.73

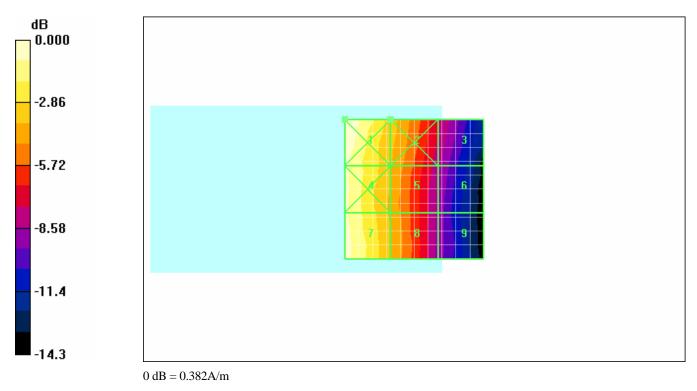
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.072 A/m; Power Drift = 0.136 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.382 M	0.262 M	0.163 M
4	4	4
Grid 4	Grid 5	Grid 6
0.359	0.248	0.148
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
0.365	0.248	0.139
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emissio rry® Smartphone model RI		Page 99(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 100(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 29/07/2008 6:37:51 PM

Test Laboratory: RTS

File Name: <u>HAC_H_GSM850_Mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 836.8 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.088 A/m; Power Drift = 0.325 dB Maximum value of Total (measured) = 0.160 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 101(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G ⁴		W	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.411 A/m

Probe Modulation Factor = 2.73

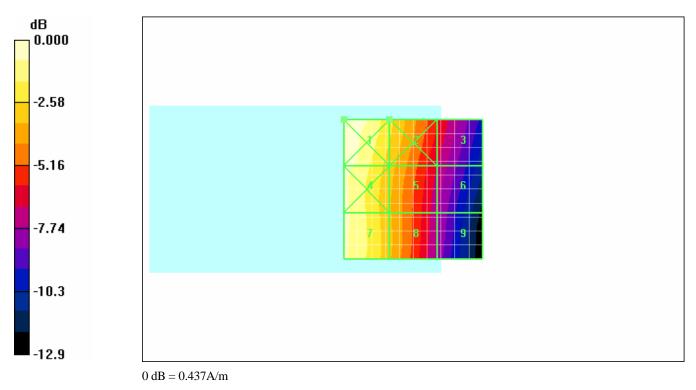
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.088 A/m; Power Drift = 0.325 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.437	0.335	0.221
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
0.417	0.309	0.199
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
0.411	0.303	0.185
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 102(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 103(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 29/07/2008 6:44:22 PM

Test Laboratory: RTS

File Name: HAC_H_GSM850_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.098 A/m; Power Drift = 0.105 dB Maximum value of Total (measured) = 0.172 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 104(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.461 A/m

Probe Modulation Factor = 2.73

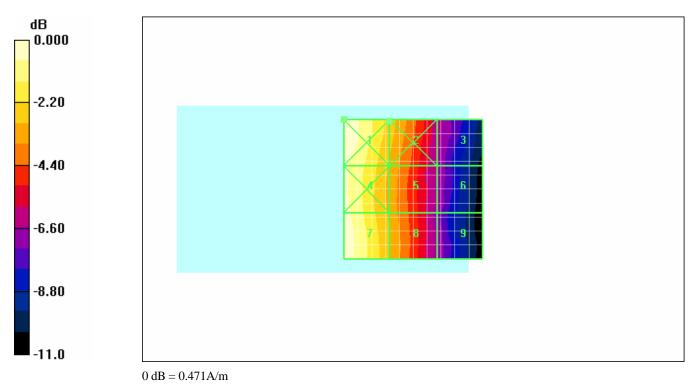
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.098 A/m; Power Drift = 0.105 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.471	0.352	0.230
Μ	Μ	Μ
3	4	4
Grid 4	Grid 5	Grid 6
0.449	0.334	0.221
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
0.461	0.338	0.217
Μ	Μ	Μ
3	4	4

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 105(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 106(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 29/07/2008 8:10:11 PM

Test Laboratory: RTS File Name: HAC_H_GSM1900_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1850.2 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.074 A/m; Power Drift = 0.004 dB Maximum value of Total (measured) = 0.086 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 107(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.197 A/m

Probe Modulation Factor = 2.74

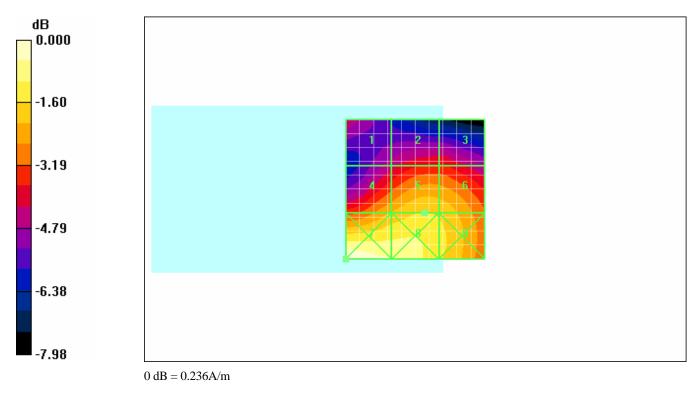
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.074 A/m; Power Drift = 0.004 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in	A/m		
Grid 1	Grid 2	Grid 3	
0.146	0.156	0.156	
Μ	Μ	Μ	
3	3	3	
Grid 4	Grid 5	Grid 6	
0.186	0.197	0.194	
Μ	Μ	Μ	
3	3	3	
Grid 7	Grid 8	Grid 9	
0.236	0.221	0.201	
Μ	Μ	Μ	
3	3	3	

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 108(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008	RTS-1115-0809-31 Rev 1	L6ARBZ40GW	



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 109(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 29/07/2008 8:16:34 PM

Test Laboratory: RTS

File Name: HAC_H_GSM1900_Mid_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1880 MHz;Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.079 A/m; Power Drift = 0.046 dB Maximum value of Total (measured) = 0.103 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 110(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Device/Hearing Aid Compatibility Test (101x101x1): Measurement

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.215 A/m

Probe Modulation Factor = 2.74

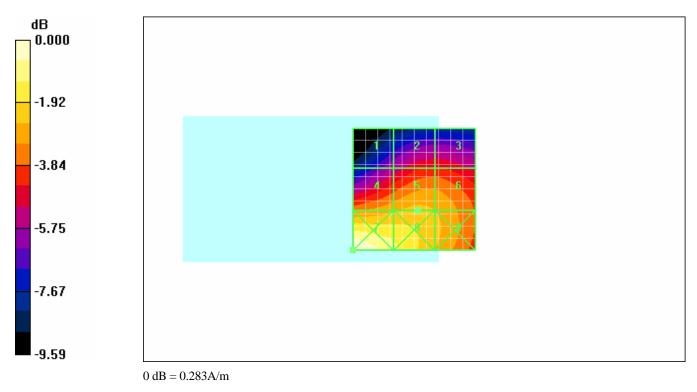
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.079 A/m; Power Drift = 0.046 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.149	0.172	0.172
Μ	Μ	Μ
3	3	3
Grid 4	Grid 5	Grid 6
0.208	0.215	0.211
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
0.283	0.250	0.216
Μ	Μ	Μ
2	3	3

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 111(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 112(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	

Date/Time: 29/07/2008 8:23:45 PM

Test Laboratory: RTS

File Name: HAC_H_GSM1900_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1909.8 MHz; Duty Cycle: 1:8.3 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.077 A/m; Power Drift = -0.031 dB Maximum value of Total (measured) = 0.113 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 113(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Device/Hearing Aid Compatibility Test (101x101x1): Measurement

grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.219 A/m

Probe Modulation Factor = 2.74

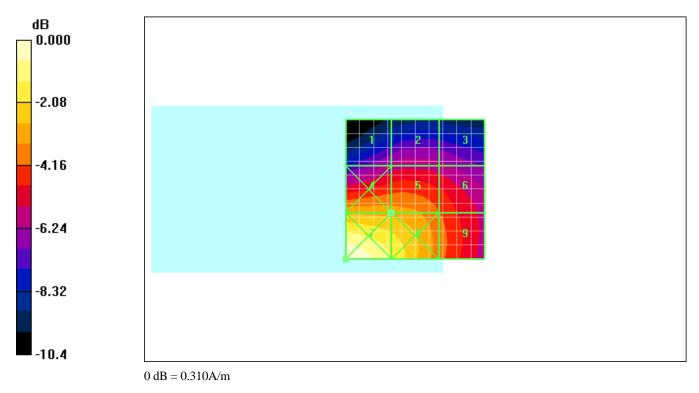
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.077 A/m; Power Drift = -0.031 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.154	0.160	0.156
Μ	Μ	Μ
3	3	3
Grid 4	Grid 5	Grid 6
0.222	0.219	0.193
Μ	Μ	Μ
3	3	3
Grid 7	Grid 8	Grid 9
0.310	0.264	0.201
Μ	Μ	Μ
2	2	3

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 114(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 115(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

Date/Time: 25/06/2008 10:44:08 AM

Test Laboratory: RTS File Name: HAC_E_Ambient Noise_835MHz.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.000 V/m; Power Drift = 999.0 dB Maximum value of Total (measured) = 1.68 V/m

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 116(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

E Scan - measurement distance from the probe sensor center to

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 1.68 V/m

Probe Modulation Factor = 1.00

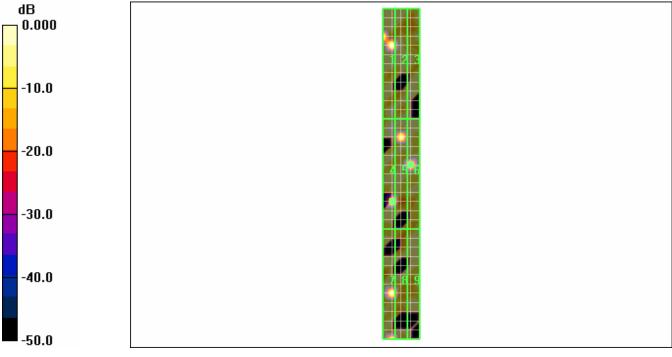
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.000 V/m; Power Drift = 999.0 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
1.57	0.408	0.000
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
1.59	1.18	1.68
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
1.50	0.596	0.000
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 117(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



 $0 \ dB = 1.68 V/m$

RTS RIM Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G			W

Date/Time: 25/06/2008 11:01:47 AM

Test Laboratory: RTS

File Name: <u>HAC_E_Ambient Noise_1880MHz.da4</u>

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1000 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.658 V/m; Power Drift = -0.581 dB Maximum value of Total (measured) = 1.69 V/m

E Scan - measurement distance from the probe sensor center to

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 119(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 1.69 V/m

Probe Modulation Factor = 1.00

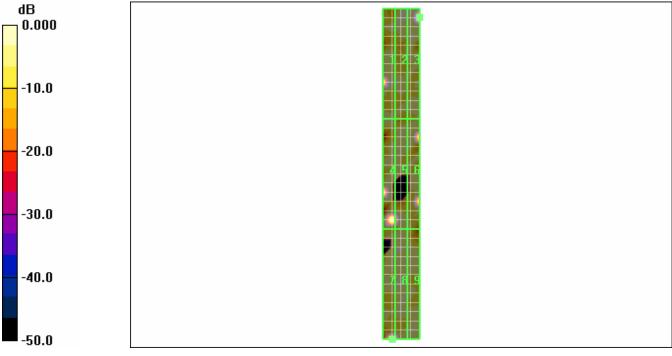
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.658 V/m; Power Drift = -0.581 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
1.09	0.000	1.60
Μ	Μ	Μ
4	4	4
Grid 4	Grid 5	Grid 6
1.55	0.470	1.14
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
1.69	0.696	0.000
Μ	Μ	\mathbf{M}
4	4	4

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 120(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40GV		W	



 $0 \ dB = 1.69 V/m$

RTS RIM Testing Services			Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW		
Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G			W	

Date/Time: 25/06/2008 2:32:22 PM

Test Laboratory: RTS

File Name: HAC_H_Ambient Noise_835MHz.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, e $_r$ = 1; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.003 A/m; Power Drift = 1.02 dB Maximum value of Total (measured) = 0.007 A/m

H Scan - measurement distance from the probe sensor center to

RTS RIM Testing Services		l Compatibility RF Emissior rry® Smartphone model RE		Page 122(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	

CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.007 A/m

Probe Modulation Factor = 1.00

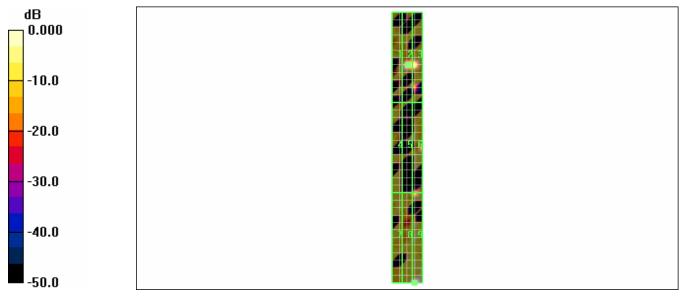
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.003 A/m; Power Drift = 1.02 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1 0.000	Grid 2 0.006	Grid 3 0.005
M 4	M 4	M 4
Grid 4	Grid 5	Grid 6
0.000	0.001	0.002
Μ	Μ	Μ
4	4	4
Grid 7	Grid 8	Grid 9
0.000	0.003	0.007
Μ	Μ	Μ
4	4	4

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 123(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G		W	



 $0 \ dB = 0.007 A/m$

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 124(126)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	July 29, Sep 26-27, 2008 RTS-1115-0809-31 Rev 1 L6ARBZ40G ³			W

Date/Time: 25/06/2008 2:41:50 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Ambient Noise_1880MHz.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium parameters used: s = 0 mho/m, $e_r = 1$; density = 1 kg/m³ Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1):

Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.001 A/m; Power Drift = 2.15 dB Maximum value of Total (measured) = 0.003 A/m

H Scan - measurement distance from the probe sensor center to

RTS RIM Testing Services		l Compatibility RF Emission rry® Smartphone model RE		Page 125(126)
Author Data	Dates of Test	Report No	FCC ID	
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CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.004 A/m

Probe Modulation Factor = 1.00

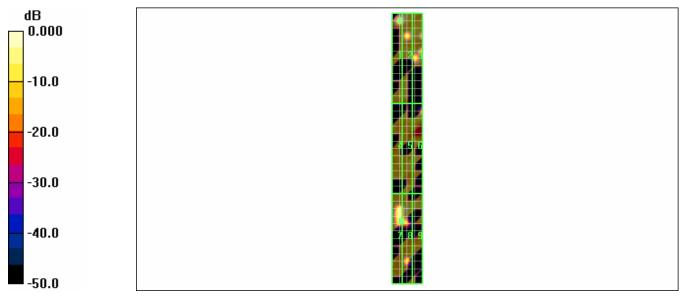
Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.001 A/m; Power Drift = 2.15 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.003	0.002	0.002
0.003	0.002	0.002
M	M	M
4	4	4
Grid 4	Grid 5	Grid 6
0.000	0.000	0.002
M 4	M 4	M 4
Grid 7	Grid 8	Grid 9
0.004	0.003	0.000
M	M	M
4	4	4

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RBZ41GW			Page 126(126)
Author Data	Dates of Test	Report No	FCC ID	
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 $0 \ dB = 0.004 A/m$